

Replaces DS5480-1.3

DFM1200FXM12-A000

Fast Recovery Diode Module

DS5480-2 April 2010 (LN26760)

FEATURES

- Low Reverse Recovery Charge .
- **High Switching Speed** .
- Low Forward Volt Drop •
- Isolated AlSiC Base with AlN Substrates •
- Dual Diodes can be paralleled for 2400A Rating
- Lead Free Construction •

APPLICATIONS

- **Chopper Diodes**
- **Boost and Buck Circuits** .
- **Free-wheel Circuits**
- **Multi-level Switch Inverters**

The DFM1200FXM12-A000 is a dual 1200V, fast recovery diode (FRD) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion.

Fast switching times and low reverse recovery losses allow high frequency operation, making the device suitable for the latest drive designs employing PWM and high frequency switching.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

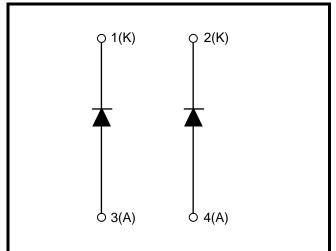
Order As:

DFM1200FXM12-A000

Note: When ordering, please use the complete part number

KEY PARAMETERS

| V _{RRM} | | 1200V |
|------------------|-------|-------|
| V _F | (typ) | 1.9V |
| I _F | (max) | 1200A |
| I _{FM} | (max) | 2400A |



External connection required for a single 2400A diode

Fig. 1 Circuit configuration

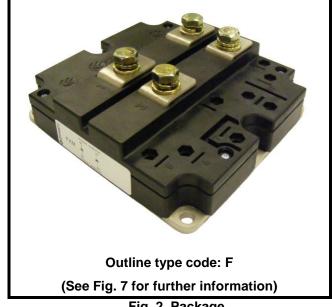


Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

| Symbol | Parameter | Test Conditions | Max. | Units |
|-------------------|--|--|------|-------------------|
| V _{RRM} | Repetitive peak reverse voltage | T _j = 125°C | 1200 | V |
| I _F | Forward current (per arm) | DC, $T_{case} = 75^{\circ}C$, $T_j = 125^{\circ}C$ | 1200 | А |
| I _{FM} | Max. forward current | $T_{case} = 110^{\circ}C, t_{p} = 1ms$ | 2400 | А |
| l ² t | I ² t value fuse current rating | $V_{R} = 0, t_{p} = 10ms, T_{j} = 125^{\circ}C$ | 400 | kA ² s |
| P _{max} | Max. transistor power dissipation | $T_{case} = 25^{\circ}C, T_{j} = 125^{\circ}C$ | 5000 | W |
| V _{isol} | Isolation voltage – per module | Commoned terminals to base plate. AC RMS, 1 min, 50Hz | 2500 | V |
| Q _{PD} | Partial discharge – per module | IEC1287, $V_1 = 1300V$, $V_2 = 1000V$, 50Hz RMS | 10 | рС |

THERMAL AND MECHANICAL RATINGS

| Internal insulation material: | AIN |
|-----------------------------------|-------|
| Baseplate material: | AlSiC |
| Creepage distance: | 20mm |
| Clearance: | 10mm |
| CTI (Comparative Tracking Index): | 350 |

| Symbol | Parameter | Test Conditions | Min | Тур. | Мах | Units |
|----------------------|--|---|-----|------|-----|-------|
| R _{th(j-c)} | Thermal resistance (per arm) | Continuous dissipation – junction to case | - | - | 20 | °C/kW |
| R _{th(c-h)} | Thermal resistance – case to heatsink (per module) | Mounting torque 5Nm (with mounting grease) | - | - | 8 | °C/kW |
| T_{j} | Junction temperature | | - | - | 125 | °C |
| T _{stg} | Storage temperature range | | -40 | - | 125 | °C |
| | | Mounting – M6 | - | - | 5 | Nm |
| | Screw Torque | Electrical connections – M8 | - | - | 10 | Nm |

STATIC ELECTRICAL CHARACTERISTICS – PER ARM

T_{case} = 25°C unless stated otherwise.

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
|-----------------|----------------------|--|-----|-----|-----|-------|
| I _{RM} | Peak reverse current | V _R = 1200V, T _j = 125°C | | | 30 | mA |
| V _F | Forward voltage | I _F = 1200A | | 1.9 | 2.2 | V |
| | | I _F = 1200A, T _j = 125°C | | 2.1 | 2.4 | V |
| L _M | Inductance | | | 20 | | nH |

STATIC ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise.

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
|----------------|---|-----------------|-----|-----|-----|-------|
| L _M | Module inductance (externally connected in parallel) | | | 15 | | nH |

DYNAMIC ELECTRICAL CHARACTERISTICS – PER ARM

T_{case} = 25°C unless stated otherwise

| Symbol | Parameter | Test Conditions | Min | Тур. | Max | Units |
|------------------|-------------------------------|--------------------------------|-----|------|-----|-------|
| Q _{rr} | Reverse recovery charge | I _F = 1200A | | 200 | | μC |
| I _{rr} | Peak reverse recovery current | $V_R = 600V$ | | 800 | | А |
| E _{rec} | Reverse recovery energy | dl _F /dt = 9000A/µs | | 80 | | mJ |

T_{case} = 125°C unless stated otherwise

| Symbol | Parameter | Test Conditions | Min | Тур. | Max | Units |
|------------------|-------------------------------|-------------------------|-----|------|-----|-------|
| Q _{rr} | Reverse recovery charge | I _F = 1200A | | 300 | | μC |
| l _{rr} | Peak reverse recovery current | $V_R = 600V$ | | 920 | | А |
| E _{rec} | Reverse recovery energy | $dI_F/dt = 8400A/\mu s$ | | 140 | | mJ |

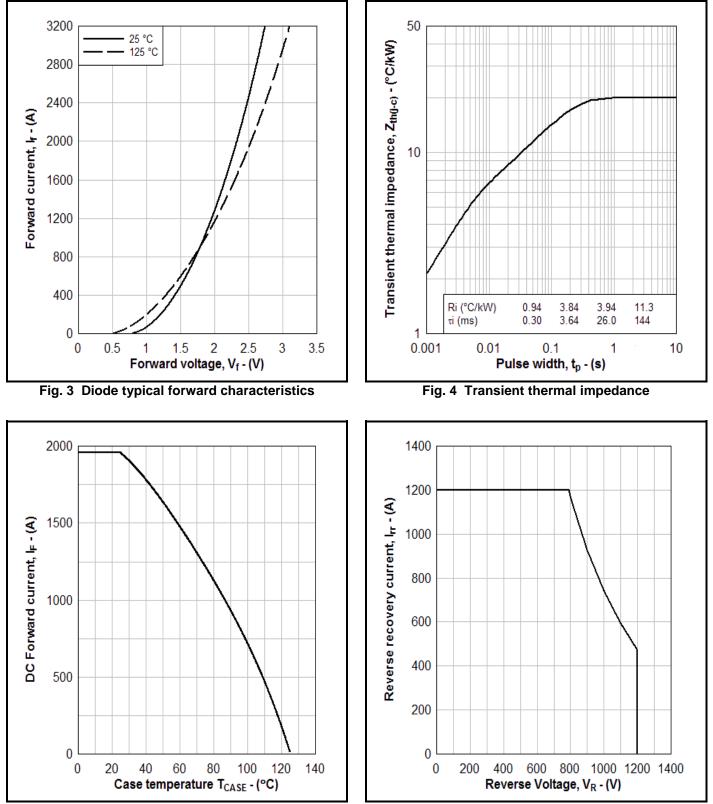
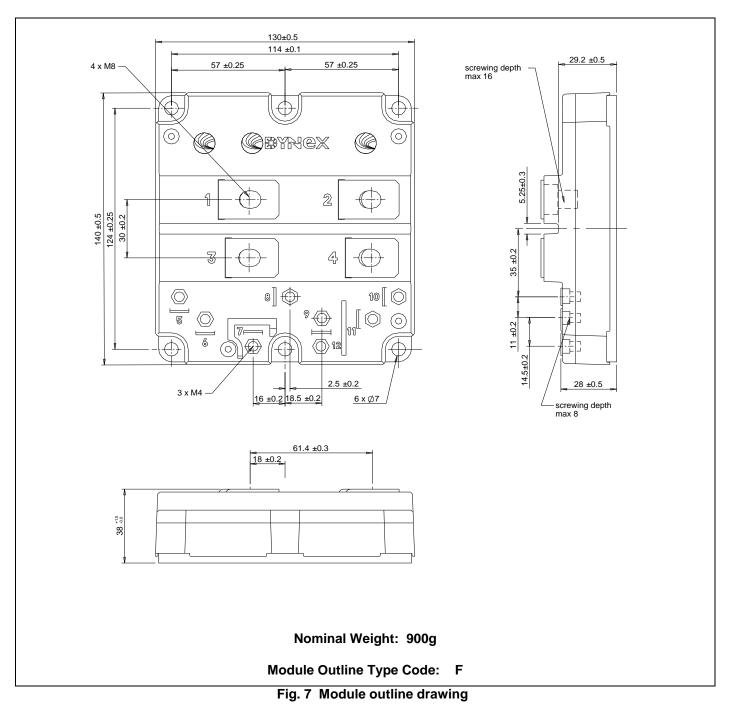


Fig. 5 DC Current rating vs case temperature

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise. **DO NOT SCALE.**



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